

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Previously Presented): A semiconductor device comprising:

a lead frame including a die pad section and leads having lead terminal sections;
a first semiconductor chip having a surface on which a first electrode section is formed, and a back surface fixed to the die pad section;

a second semiconductor chip having a surface on which a second electrode section is formed, and a back surface fixed to the surface of the first semiconductor chip;

a support member having a surface fixed to the back surface of the second semiconductor chip and a back surface fixed to the die pad section,

the lead terminal sections respectively electrically connected to the first and second electrode sections; and

a resin encapsulating body that seals the die pad section, the first and second semiconductor chips and the support member,

wherein a first side surface of the support member is located directly under the second semiconductor chip, and a second side surface of the support member opposite the first side surface is located out from under the second semiconductor chip.

Claim 2 (Original): A semiconductor device according to claim 1, wherein the first semiconductor chip and the second semiconductor chip respectively have electric circuits each having the same function.

Claim 3 (Original): A semiconductor device according to claim 1, wherein the first semiconductor chip and the second semiconductor chip have the same shape and size respectively.

Claim 4 (Original): A semiconductor device according to claim 1, wherein the support member is formed in isolation from the first semiconductor chip.

Claims 5-6 (Canceled)

Claim 7 (Previously Presented): A semiconductor device according to claim 1, wherein the surface of the first semiconductor chip has first and second sides opposite to each other,

the surface of the second semiconductor chip has third and fourth sides opposite to each other, and

the fourth side of the second semiconductor chip protrudes from the second side of the first semiconductor chip, and the fourth side thereof is located directly above the support member.

Claims 8-11 (Canceled)

Claim 12 (Previously Presented): A semiconductor device according to claim 1, wherein the first and second semiconductor chips extend in a same first direction so as to be disposed in parallel with respect to each other.

Claim 13 (Previously Presented): A semiconductor device according to claim 1, wherein the first side surface of the support member, and a side surface of the first semiconductor chip that opposes the first side surface, directly contact each other.

Claim 14 (Previously Presented): A semiconductor device according to claim 1, wherein a gap exists between the first side surface of the support member and a side surface of the first semiconductor chip that opposes the first side surface.

Claim 15 (Previously Presented): A semiconductor device according to claim 1, wherein a portion of the back surface of the first semiconductor chip is fixed to inner portions of the lead terminal sections that are within the resin encapsulating body.

Claim 16 (Previously Presented): A semiconductor device according to claim 15, wherein the die pad section and the lead terminal sections are part of the lead frame.

Claim 17 (Previously Presented): A semiconductor device according to claim 1, wherein the support member is an insulator.

Claim 18 (Previously Presented): A semiconductor device according to claim 1, wherein the support member is a conductor.

Claim 19 (Previously Presented): A semiconductor device comprising:

a lead frame including a die pad section and leads having lead terminal sections;

a first semiconductor chip having a surface on which a first electrode section is formed, and a back surface fixed to the die pad section;

a second semiconductor chip having a surface on which a second electrode section is formed, and a back surface fixed to the surface of the first semiconductor chip;

a support member having a surface fixed to the back surface of the second semiconductor chip and a back surface fixed to the die pad section and first portions of the lead terminal sections;

wirings respectively electrically connecting the first and second electrode sections to the first portions of the lead terminal sections; and

a resin encapsulating body that seals the die pad section, the first portions of the lead terminal sections, the first and second semiconductor chips and the support member.

Claim 20 (Previously Presented): A semiconductor device according to claim 19, wherein a first side surface of the support member is located directly under the second semiconductor chip, and a second side surface of the support member opposite the first side surface is located out from under the second semiconductor chip.

Claim 21 (Previously Presented): A semiconductor device according to claim 19, wherein the first and second semiconductor chips extend in a same first direction so as to be disposed in parallel with respect to each other.

Claim 22 (Previously Presented): A semiconductor device according to claim 19, wherein a first side surface of the support member, and a side surface of the first semiconductor chip that opposes the first side surface, directly contact each other.

Claim 23 (Previously Presented): A semiconductor device according to claim 19, wherein a gap exists between a first side surface of the support member and a side surface of the first semiconductor chip that opposes the first side surface.

Claim 24 (Previously Presented): A semiconductor device according to claim 19, wherein the support member is an insulator.

Claim 25 (Previously Presented): A semiconductor device according to claim 19,

wherein the support member is a conductor.

Claim 26 (Previously Presented): A semiconductor device according to claim 1, wherein the support member is formed integrally with the first semiconductor chip.

Claim 27 (Currently Amended): A semiconductor device according to claim 26 ~~[[5]]~~, wherein the first semiconductor chip and the support member are formed in a semiconductor wafer and thereafter formed separately in an integral state.